

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

PATENT APPLICATION

Inventor(s): HOSHINO et al.

Appln. No.: 09

835,820

Series Code ↑

Serial No. ↑

Filed: April 17, 2001

Hon. Commissioner of Patents

Washington, D.C. 20231

Group Art Unit

2825

Examiner:

C. LUU

Atty. Dkt.

P

280192

EL00028CDC

Client Ref

Appln. Title:

FABRICATION PROCESS OF A
SEMICONDUCTOR DEVICE
INCLUDING A CVD PROCESS OF A
METAL FILM

Sir:

REPLY/AMENDMENT/LETTER

Date: December 2, 2002

This is a reply/amendment/letter in the above-identified application and includes the herewith attachment of same date and subject which is incorporated herein by reference and the signature below is treated as the signature to the attachment in absence of a signature thereto.

FEE REQUIREMENTS FOR CLAIMS AS AMENDED

1. Small Entity claim A. <input checked="" type="checkbox"/> NOT made B. <input type="checkbox"/> Withdrawn C. <input type="checkbox"/> made herewith D. <input type="checkbox"/> made previously For B & C See Required Separate Paper (Pat-256)		Claims remaining after amendment	Highest number previously paid for	Present Extra	Large/Small Entity	Additional Fee	Fee Code Lg/Sm
2. Total Effective Claims		16	**minus 20	0	x \$18/\$9 =	+ \$0	103/203
3. Independent Claims		3	***minus 3	0	x \$84/\$42 =	+ \$0	102/202
4. If amendment enters proper multiple dependent claim(s) into this application for first time (leave blank if this is a reissue application) add					+ \$280/\$140 =	+ \$0	104/204
5. Original due Date: October 1, 2002		<input type="checkbox"/> NONE					
6. Petition is hereby made to extend the original due date to cover the date this response is filed for which the requisite fee is attached		(1 mo)	\$110/\$55 =				115/215
		(2 mos)	\$400/\$200 =	+ \$400			116/216
		(3 mos)	\$920/\$460 =				117/217
		(4 mos)	\$1,440/\$720 =				118/218
		(5 mos)	\$1,960/\$980 =				128/228
7. Enter any previous extension fee paid since above original due date and subtract					- \$0		
8. Extension Fee					+ \$400		
9. If Terminal Disclaimer attached, add Rule 20(d) official fee					+ \$110/\$55	+ \$0	148/248
10. If IDS attached requires Official Fee under Rule 97 (c), add					+ \$180	+ \$0	126
or if Rule 97(d) Request add					+ \$180		126
11. After-Final Request Fee per rules 129(a) and 17(r)					+ \$740/370	+ \$0	146/246
12. No. of additional inventions for examination per Rule 129(b)					x \$740/370 ea	+ \$0	149/249
13. Request for Continued Examination (RCE)					+ \$740/370	+ \$0	1179/1279
14. Petition fee for					+ \$0		
15. TOTAL FEE =					\$400		
16. *If the entry in this space is less than entry in next space, the "Present Extra" result is "0".					PLEASE CHARGE OUR DEP. ACCT		
17. **If the "Highest number previously paid for" in this space is less than 20, write "20" in this space.							
18. ***If the "Highest number previously paid for" in this space is less than 3, write "3" in this space.							

Our Deposit Account No. 03-3975)

(Our Order No. 40258

280192

C#

M#

CHARGE STATEMENT: The Commissioner is hereby authorized to charge any fee specifically authorized hereafter, or any missing or insufficient fee(s) filed, or asserted to be filed, or which should have been filed herewith or concerning any paper filed hereafter, and which may be required under Rules 16-18 (missing or insufficiencies only) now or hereafter relative to this application and the resulting Official Document under Rule 20, or credit any overpayment, to our Accounting/Order Nos. shown above, for which purpose a duplicate copy of this sheet is attached.

This CHARGE STATEMENT does not authorize charge of the issue fee until/unless an issue fee transmittal sheet is filed.

Query: Is appeal deadline now? If so, file Notice of Appeals separately.

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Intellectual Property Group

By Atty: Glenn J. Perry

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NOTE: File this cover sheet in duplicate with PTO receipt (PAT-103A) and attachments



#9/B
Dlms
12-9-02

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TECHNOLOGY CENTER 2800

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT APPLICATION OF

Confirmation No.: 55392

HOSHINO et al.

Group Art Unit: 2825 2800

Appln. No.: 09/835,820

Examiner: C. LUU

Filed: April 17, 2001

Title: FABRICATION PROCESS OF A SEMICONDUCTOR DEVICE INCLUDING A CVD
PROCESS OF A METAL FILM

December 1, 2002 (Sunday)
December 2, 2002 (Monday)

* * * * *

AMENDMENT

Hon. Commissioner of Patents
Washington, D.C. 20231

Sir:

In response to the Office Action dated July 1, 2002, please amend the above
identified application as follows:

IN THE SPECIFICATION:

Please substitute the following for the paragraphs appearing in the original
specification:

Page 4, third full paragraph:

Another object of the present invention is to provide a method for fabricating a
semiconductor device, comprising the steps of:

forming a barrier conductor layer on a substrate;

12/04/2002 DTESSEH1 00000008 033975 09835820

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